

## M41ST85Y M41ST85W

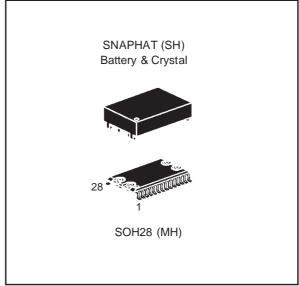
# 512 Kbit (64 bit x 8) Serial Access RTC and NVRAM SUPERVISOR

PRELIMINARY DATA

#### **FEATURES SUMMARY**

- 3V or 5V OPERATING VOLTAGE
- SERIAL INTERFACE SUPPORTS I<sup>2</sup>C BUS (400 KHz)
- NVRAM SUPERVISOR for EXTERNAL LPSRAM
- OPTIMIZED for MINIMAL INTERCONNECT to MCU
- 2.5 to 5.5V CLOCK OPERATING VOLTAGE
- AUTOMATIC SWITCH-OVER and DESELECT CIRCUITRY
- CHOICE of POWER-FAIL DESELECT VOLTAGES
  - M41ST85Y:  $V_{CC}$  = 4.5 to 5.5V;  $V_{PFD}$  = 4.40  $\pm$  0.10V
  - M41ST85W:  $V_{CC}$  = 2.7 to 3.6V;  $V_{PFD}$  = 2.65  $\pm$  0.05V
- 1.25V REFERENCE (for PFI/PFO)
- COUNTERS FOR TENTHS/HUNDREDTHS of SECONDS, SECONDS, MINUTES, HOURS, DAY, DATE, MONTH, YEAR, and CENTURY
- 44 BYTES of GENERAL PURPOSE RAM
- PROGRAMMABLE ALARM AND INTERRUPT FUNCTION (VALID EVEN DURING BATTERY BACK-UP MODE)
- WATCHDOG TIMER
- MICROPROCESSOR POWER-ON RESET
- BATTERY LOW FLAG
- ULTRA-LOW BATTERY SUPPLY CURRENT of 500nA (MAX)
- PACKAGING INCLUDES a 28-LEAD SOIC and SNAPHAT TOP (to be Ordered Separately)
- SOIC PACKAGE PROVIDES DIRECT CONNECTION for a SNAPHAT TOP WHICH CONTAINS the BATTERY and CRYSTAL

Figure 1. Packages



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## M41ST85Y, M41ST85W

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#### SUMMARY DESCRIPTION

The M41ST85Y/W Serial TIMEKEEPER/Controller SRAM is a low power 512 bit static CMOS SRAM organized as 64 words by 8 bits. A built-in 32.768 kHz oscillator (external crystal controlled) and 8 bytes of the SRAM (see Table 6, page 19) are used for the clock/calendar function and are configured in binary coded decimal (BCD) format.

An additional 12 bytes of RAM provide status/control of Alarm, Watchdog and Square Wave functions. Addresses and data are transferred serially via a two line, bi-directional I<sup>2</sup>C interface. The built-in address register is incremented automatically after each write or read data byte. The M41ST85Y/W has a built-in power sense circuit which detects power failures and automatically switches to the battery supply when a power failure occurs. The energy needed to sustain the SRAM and clock operations can be supplied by a small lithium button-cell supply when a power failure occurs.

Functions available to the user include a non-volatile, time-of-day clock/calendar, Alarm interrupts, Watchdog Timer and programmable Square Wave output. Other features include a Power-On Reset as well as two additional debounced inputs (RSTIN1 and RSTIN2) which can also generate an output Reset (RST). The eight clock address locations contain the century, year, month, date, day, hour, minute, second and tenths/hundredths of a second in 24 hour BCD format. Corrections for 28,

29 (leap year - valid until year 2100), 30 and 31 day months are made automatically. The ninth clock address location controls user access to the clock information and also stores the clock software calibration setting.

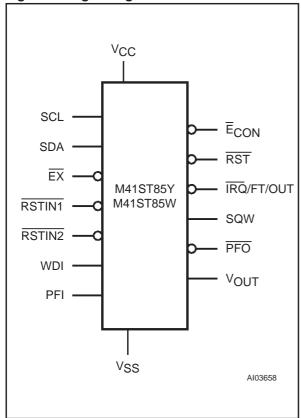
The M41ST85Y/W is supplied in a 28 lead SOIC SNAPHAT package (which integrates both crystal and battery in a single SNAPHAT top). The 28 pin 330mil SOIC provides sockets with gold plated contacts at both ends for direct connection to a separate SNAPHAT housing containing the battery and crystal. The unique design allows the SNAPHAT battery/crystal package to be mounted on top of the SOIC package after the completion of the surface mount process.

Insertion of the SNAPHAT housing after reflow prevents potential battery and crystal damage due to the high temperatures required for device surface-mounting. The SNAPHAT housing is also keyed to prevent reverse insertion.

The SOIC and battery/crystal packages are shipped separately in plastic anti-static tubes or in Tape & Reel form. For the 28 lead SOIC, the battery/crystal package (i.e. SNAPHAT) part number is "M4TXX-BR12SH" (see Table 18, page 30).

**Caution:** Do not place the SNAPHAT battery/crystal top in conductive foam, as this will drain the lithium button-cell battery.

Figure 2. Logic Diagram



**Table 1. Signal Names** 

E <sub>CON</sub>	Conditioned Chip Enable Output
-CON	Conditioned Only Enable Output
ĒΧ	External Chip Enable
ĪRQ/FT/OUT	Interrupt/Frequency Test/Out Output (Open Drain)
PFI	Power Fail Input
PFO	Power Fail Output
RST	Reset Output (Open Drain)
RSTIN1	Reset 1 Input
RSTIN2	Reset 2 Input
SCL	Serial Clock Input
SDA	Serial Data Input/Output
SQW	Square Wave Output
WDI	Watchdog Input
V <sub>CC</sub>	Supply Voltage
V <sub>OUT</sub>	Voltage Output
V <sub>SS</sub>	Ground

Figure 3. SOIC Connections

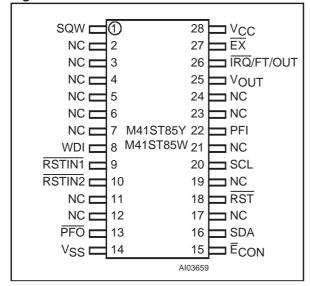


Figure 4. Block Diagram

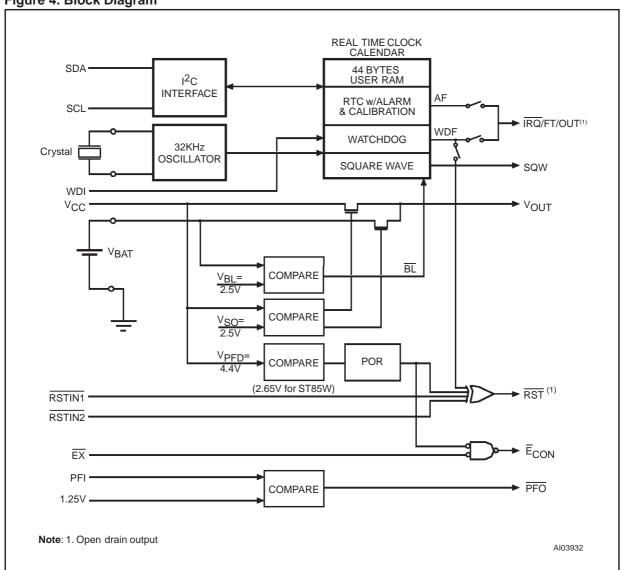
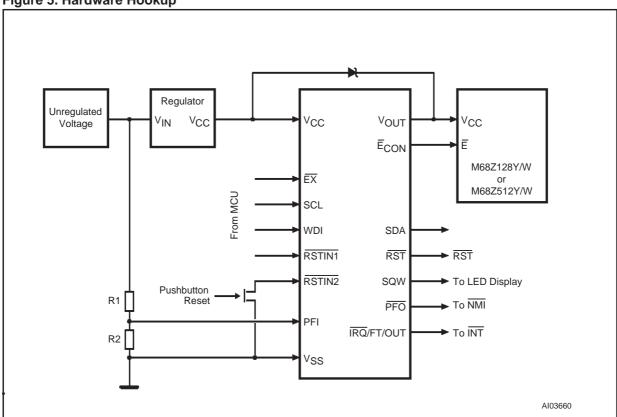


Figure 5. Hardware Hookup



#### **OPERATING MODES**

The M41ST85Y/W clock operates as a slave device on the serial bus. Access is obtained by implementing a start condition followed by the correct slave address (D0h). The 64 bytes contained in the device can then be accessed sequentially in the following order:

- 1. Tenths/Hundredths of a Second Register
- 2. Seconds Register
- 3. Minutes Register
- 4. Century/Hours Register
- 5. Day Register
- 6. Date Register
- 7. Month Register
- 8. Year Register
- 9. Control Register
- 10. Watchdog Register
- 11 16. Alarm Registers
- 17 19. Reserved
- 20. Square Wave Register
- 21 64. User RAM

The M41ST85Y/W clock continually monitors  $V_{CC}$  for an out-of tolerance condition. Should  $V_{CC}$  fall below  $V_{PFD}$ , the device terminates an access in progress and resets the device address counter. Inputs to the device will not be recognized at this time to prevent erroneous data from being written to the device from a an out-of-tolerance system. When  $V_{CC}$  falls below  $V_{SO}$ , the device automatically switches over to the battery and powers down into an ultra low current mode of operation to conserve battery life. As system power returns and  $V_{CC}$  rises above  $V_{SO}$ , the battery is disconnected, and the power supply is switched to external  $V_{CC}$ . Write protection continues until  $V_{CC}$  reaches  $V_{PFD}$  plus  $t_{REC}$ .

For more information on Battery Storage Life refer to Application Note AN1012.

#### 2-Wire Bus Characteristics

The bus is intended for communication between different ICs. It consists of two lines: a bi-directional data signal (SDA) and a clock signal (SCL). Both the SDA and SCL lines must be connected to a positive supply voltage via a pull-up resistor.

The following protocol has been defined:

 Data transfer may be initiated only when the bus is not busy.

- During data transfer, the data line must remain stable whenever the clock line is High.
- Changes in the data line, while the clock line is High, will be interpreted as control signals.

Accordingly, the following bus conditions have been defined:

**Bus not busy.** Both data and clock lines remain High.

**Start data transfer.** A change in the state of the data line, from High to Low, while the clock is High, defines the START condition.

**Stop data transfer.** A change in the state of the data line, from Low to High, while the clock is High, defines the STOP condition.

**Data Valid.** The state of the data line represents valid data when after a start condition, the data line is stable for the duration of the high period of the clock signal. The data on the line may be changed during the Low period of the clock signal. There is one clock pulse per bit of data.

Each data transfer is initiated with a start condition and terminated with a stop condition. The number of data bytes transferred between the start and stop conditions is not limited. The information is transmitted byte-wide and each receiver acknowledges with a ninth bit.

By definition a device that gives out a message is called "transmitter", the receiving device that gets the message is called "receiver". The device that controls the message is called "master". The devices that are controlled by the master are called "slaves".

Acknowledge. Each byte of eight bits is followed by one acknowledge bit. This acknowledge bit is a low level put on the bus by the receiver whereas the master generates an extra acknowledge related clock pulse. A slave receiver which is addressed is obliged to generate an acknowledge after the reception of each byte that has been clocked out of the slave transmitter.

The device that acknowledges has to pull down the SDA line during the acknowledge clock pulse in such a way that the SDA line is a stable Low during the High period of the acknowledge related clock pulse. Of course, setup and hold times must be taken into account. A master receiver must signal an end of data to the slave transmitter by not generating an acknowledge on the last byte that has been clocked out of the slave. In this case the transmitter must leave the data line High to enable the master to generate the STOP condition.

Figure 6. Serial Bus Data Transfer Sequence

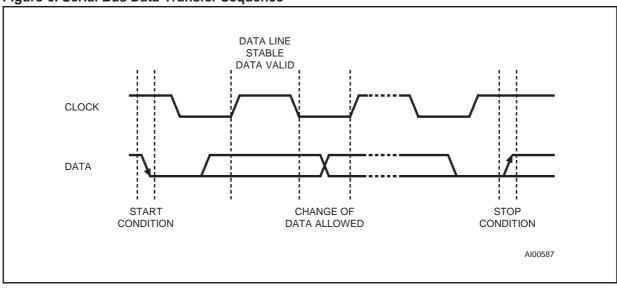


Figure 7. Acknowledgement Sequence

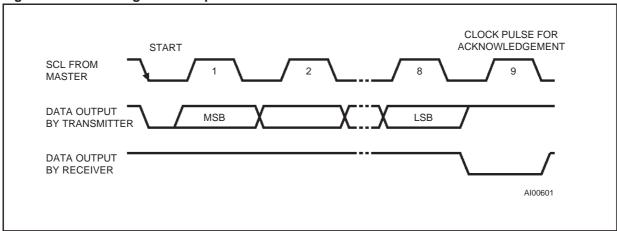


Figure 8. Write Cycle Timing: RTC & External SRAM Control Signals

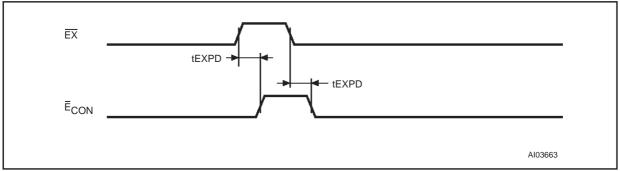
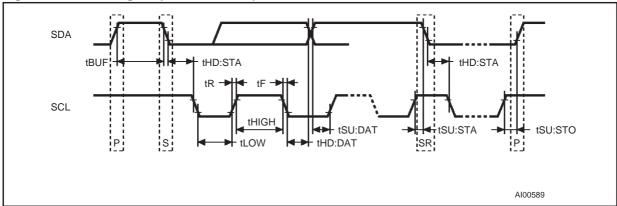


Figure 9. Bus Timing Requirements Sequence



**Table 2. AC Characteristics** 

Symbol	Parameter		Min	Max	Unit
f <sub>SCL</sub>	SCL Clock Frequency		0	400	kHz
t <sub>BUF</sub>	Time the bus must be free before a new transm	ission can start	1.3		μs
tevan	EX to E <sub>CON</sub> Propagation Delay	M41ST85Y		10	ns
tEXPD	LX to ECON Propagation Delay	M41ST85W		15	115
t <sub>F</sub>	SDA and SCL Fall Time			300	ns
thd:dat	Data Hold Time		0		μs
t <sub>HD:STA</sub>	START Condition Hold Time (after this period the first clock pulse is generated)		600		ns
tHIGH	Clock High Period		600		ns
t <sub>LOW</sub>	Clock Low Period		1.3		μs
t <sub>R</sub>	SDA and SCL Rise Time			300	ns
t <sub>SU:DAT</sub> <sup>(1)</sup>	Data Setup Time		100		ns
t <sub>SU:STA</sub>	START Condition Setup Time (only relevant for a repeated start condition)		600		ns
t <sub>SU:STO</sub>	STOP Condition Setup Time		600		ns

Note: 1. Transmitter must internally provide a hold time to bridge the undefined region (300ns max) of the falling edge of SCL.

#### **Read Mode**

In this mode the master reads the M41ST85Y/W slave after setting the slave address (see Figure 10, page 12). Following the write mode control bit (R/W=0) and the acknowledge bit, the word address 'An' is written to the on-chip address pointer. Next the START condition and slave address are repeated followed by the READ mode control bit (R/W=1). At this point the master transmitter becomes the master receiver.

The data byte which was addressed will be transmitted and the master receiver will send an acknowledge bit to the slave transmitter. The address pointer is only incremented on reception of an acknowledge bit. The M41ST85Y/W slave transmitter will now place the data byte at address An+1 on the bus, the master receiver reads and acknowledges the new byte and the address pointer is incremented to An+2.

This cycle of reading consecutive addresses will continue until the master receiver sends a STOP condition to the slave transmitter (see Figure 11, page 12).

The system-to-user transfer of clock data will be halted whenever the address being read is a clock address (00h to 07h). The update will resume either due to a Stop Condition or when the pointer increments to a RAM address.

An alternate READ mode may also be implemented whereby the master reads the M41ST85Y/W slave without first writing to the (volatile) address pointer. The first address that is read is the last one stored in the pointer (see Figure 12, page 12).

#### Write Mode

In this mode the master transmitter transmits to the M41ST85Y/W slave receiver. Bus protocol is shown in Figure 13, page 13. Following the START condition and slave address, a logic '0' (R/ $\overline{W}$ =0) is placed on the bus and indicates to the addressed device that word address An will follow and is to be written to the on-chip address pointer. The data word to be written to the memory is strobed in next and the internal address pointer is incremented to the next memory location within

the RAM on the reception of an acknowledge clock. The M41ST85Y/W slave receiver will send an acknowledge clock to the master transmitter after it has received the slave address (see Figure 10, page 12) and again after it has received the word address and each data byte.

## **Battery Low Warning**

The M41ST85Y/W automatically performs battery voltage monitoring upon power-up and at factory-programmed time intervals of approximately 24 hours. The Battery Low (BL) bit, Bit D4 of Flags Register 0Fh, will be asserted if the battery voltage is found to be less than approximately 2.5V. The BL bit will remain asserted until completion of battery replacement and subsequent battery low monitoring tests, either during the next power-up sequence or the next scheduled 24-hour interval.

If a battery low is generated during a power-up sequence, this indicates that the battery is below approximately 2.5 volts and may not be able to maintain data integrity in the SRAM. Data should be considered suspect and verified as correct. A fresh battery should be installed.

If a battery low indication is generated during the 24-hour interval check, this indicates that the battery is near end of life. However, data is not compromised due to the fact that a nominal  $V_{CC}$  is supplied. In order to insure data integrity during subsequent periods of battery back-up mode, the battery should be replaced. The SNAPHAT top may be replaced while  $V_{CC}$  is applied to the device.

**Note**: This will cause the clock to lose time during the interval the SNAPHAT battery/crystal top is disconnected.

The M41ST85Y/W only monitors the battery when a nominal  $V_{CC}$  is applied to the device. Thus applications which require extensive durations in the battery back-up mode should be powered-up periodically (at least once every few months) in order for this technique to be beneficial. Additionally, if a battery low is indicated, data integrity should be verified upon power-up via a checksum or other technique.

Figure 10. Slave Address Location

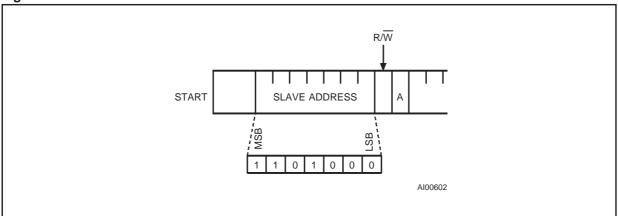


Figure 11. Read Mode Sequences

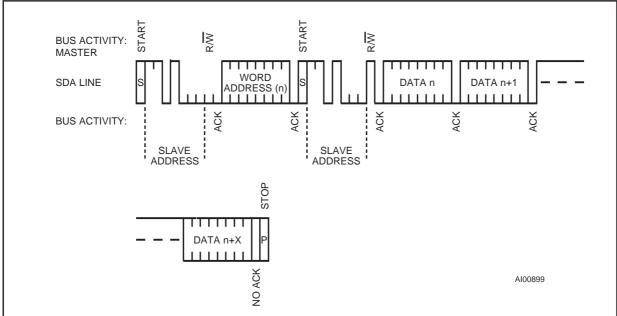


Figure 12. Alternate Read Mode Sequences

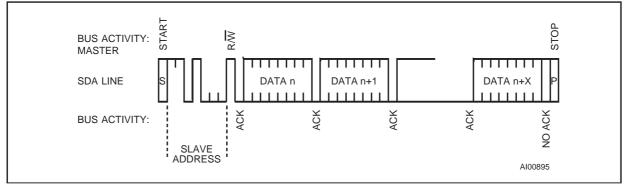
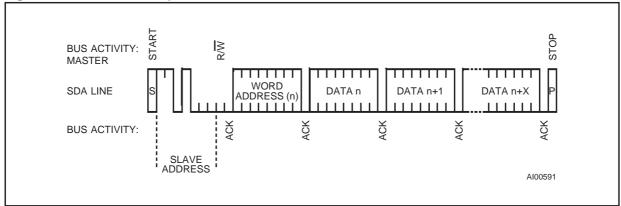


Figure 13. Write Mode Sequence



#### **CLOCK OPERATION**

The eight byte clock register (see Table 3, page 15) is used to both set the clock and to read the date and time from the clock, in a binary coded decimal format. Tenths/Hundredths of Seconds, Seconds, Minutes, and Hours are contained within the first four registers. Bits D6 and D7 of clock register 3 (Century/Hours Register) contain the CEN-TURY ENABLE Bit (CEB) and the CENTURY Bit (CB). Setting CEB to a '1' will cause CB to toggle, either from '0' to '1' or from '1' to '0' at the turn of the century (depending upon its initial state). If CEB is set to a '0', CB will not toggle. Bits D0 through D2 of register 4 contain the Day (day of week). Registers 5, 6 and 7 contain the Date (day of month), Month and Years. The ninth clock register is the Control Register (this is described in the Clock Calibration section). Bit D7 of register 1 contains the STOP Bit (ST). Setting this bit to a '1' will cause the oscillator to stop. If the device is expected to spend a significant amount of time on the shelf, the oscillator may be stopped to reduce current drain. When reset to a '0' the oscillator restarts within one second.

The eight Clock Registers may be read one byte at a time, or in a sequential block. The Control Register (Address location 08h) may be accessed independently. Provision has been made to assure that a clock update does not occur while any of the seven clock addresses are being read. If a clock address is being read, an update of the clock registers will be halted. This will prevent a transition of data during the read.

**Note:** Upon power-up following a power failure, the HT bit will automatically be set to a '1'. This will prevent the clock from updating the TIMEKEEPER registers, and will allow the user to read the exact time of the power-down event. Resetting the HT bit to a '0' will allow the clock to update the TIME-KEEPER registers with the current time.

## **Data Retention Mode**

With valid V<sub>CC</sub> applied, the M41ST85Y/W can be accessed as described above with read or write cycles. Should the supply voltage decay, the M41ST85Y/W will automatically deselect, write protecting itself (and any external SRAM) when V<sub>CC</sub> falls between V<sub>PFD</sub> (max) and V<sub>PFD</sub> (min). This is accomplished by internally inhibiting access to the clock registers. At this time, the Reset pin ( $\overline{RST}$ ) is driven active and will remain active until V<sub>CC</sub> returns to nominal levels. External RAM access is inhibited in a similar manner by

forcing  $\overline{E}_{CON}$  to a high level. This level is within 0.2 volts of the  $V_{BAT}$ .  $\overline{E}_{CON}$  will remain at this level as long as  $V_{CC}$  remains at an out-of tolerance condition. When  $V_{CC}$  falls below the Battery Back-up Switchover Voltage ( $V_{SO}$ ), power input is switched from the  $V_{CC}$  pin to the SNAPHAT battery and the clock registers and external SRAM are maintained from the attached battery supply.

All outputs become high impedance. The  $V_{OUT}$  pin is capable of supplying 100  $\mu A$  of current to the attached memory with less than 0.3 volts drop under this condition. On power up, when  $V_{CC}$  returns to a nominal value, write protection continues for  $t_{REC}$  by inhibiting  $\overline{E}_{CON}$ . The  $\overline{RST}$  signal also remains active during this time (see Figure 21, page 26).

**Note:** Most low power SRAMs on the market today can be used with the M41ST85Y/W RTC SUPERVISOR. There are, however some criteria which should be used in making the final choice of an SRAM to use. The SRAM must be designed in a way where the chip enable input disables all other inputs to the SRAM. This allows inputs to the M41ST85Y/W and SRAMs to be Don't Care once  $V_{CC}$  falls below  $V_{PFD}$ (min). The SRAM should also guarantee data retention down to  $V_{CC}$ =2.0 volts. The chip enable access time must be sufficient to meet the system needs with the chip enable output propagation delays included. If the SRAM includes a second chip enable pin (E2), this pin should be tied to  $V_{OUT}$ .

If data retention lifetime is a critical parameter for the system, it is important to review the data retention current specifications for the particular SRAMs being evaluated. Most SRAMs specify a data retention current at 3.0 volts. Manufacturers generally specify a typical condition for room temperature along with a worst case condition (generally at elevated temperatures). The system level requirements will determine the choice of which value to use. The data retention current value of the SRAMs can then be added to the IBAT value of the M41ST85Y/W to determine the total current requirements for data retention. The available battery capacity for the SNAPHAT of your choice can then be divided by this current to determine the amount of data retention available (see Table 18, page 30).

For a further more detailed review of lifetime calculations, please see Application Note AN1012.

## TIMEKEEPER® Registers

The M41ST85Y/W offers 20 internal registers which contain Clock, Alarm, Watchdog, Flag, Square Wave and Control data. These registers are memory locations which contain external (user accessible) and internal copies of the data (usually referred to as BiPORT<sup>TM</sup> TIMEKEEPER cells).

The external copies are independent of internal functions except that they are updated periodically by the simultaneous transfer of the incremented internal copy. TIMEKEEPER and Alarm Registers store data in BCD. Control, Watchdog and Square Wave Registers store data in Binary Format.

**Table 3. TIMEKEEPER Register Map** 

Address				Da	ıta				Function/Range	
Address	D7	D6	D5	D4	D3	D2	D1	D0	BCD Fo	rmat
00h		0.1 Se	conds		0.01 Seconds				Seconds	00-99
01h	ST	1	0 Second	ls		Seco	onds		Seconds	00-59
02h	0	1	0 Minute	S		Min	utes		Minutes	00-59
03h	CEB	СВ	10 H	lours	Но	urs (24 H	lour Form	at)	Century/Hour	0-1/00-23
04h	0	0	0	0	0	D	ay of Wee	ek	Day	01-7
05h	0	0	10 [	Date	ı	Date: Day	of Month	1	Date	01-31
06h	0	0	0	10M		Мо	nth		Month	01-12
07h		10 Years				Ye	ar		Year	00-99
08h	OUT	FT	S		(	Calibration	า		Control	
09h	WDS	BMB4	BMB3	BMB2	BMB1	вмво	RB1	RB0	Watchdog	
0Ah	AFE	SQWE	ABE	Al 10M		Alarm	Month	_	Al Month	01-12
0Bh	RPT4	RPT5	AI 10	Date		Alarm	Date		Al Date	01-31
0Ch	RPT3	HT	AI 10	Hour		Alarm	Hour		Al Hour	00-23
0Dh	RPT2	Alar	Alarm 10 Minutes			Alarm I	Minutes		Al Min	00-59
0Eh	RPT1	Alarr	n 10 Sec	onds		Alarm S	Seconds		Al Sec	00-59
0Fh	WDF	AF	0	BL	0	0	0	0	Flags	
10h	0	0	0	0	0	0	0	0	Reserved	
11h	0	0	0	0	0 0 0 0		Reserved			
12h	0	0	0	0	0 0 0 0		Reserved			
13h	RS3	RS2	RS1	RS0	0	0	0	0	SQW	

Keys: S = Sign Bit

FT = Frequency Test Bit

ST = Stop Bit

0 = Must be set to zero

BL = Battery Low Flag

BMB0-BMB4 = Watchdog Multiplier Bits

CEB = Century Enable Bit

CB = Century Bit

OUT = Output level

AFE = Alarm Flag Enable Flag

RB0-RB1 = Watchdog Resolution Bits

WDS = Watchdog Steering Bit

ABE = Alarm in Battery Back-Up Mode Enable Bit

RPT1-RPT5 = Alarm Repeat Mode Bits

WDF = Watchdog flag

AF = Alarm flag

SQWE = Square Wave Enable

RS0-RS3 = SQW Frequency

HT = Halt Update Bit

## **Setting Alarm Clock Registers**

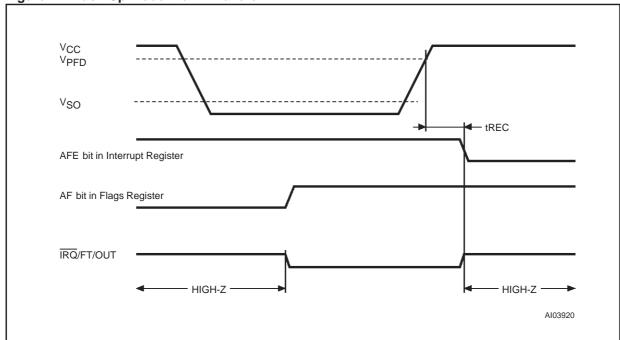
Address locations 0Ah-0Eh contain the alarm settings. The alarm can be configured to go off at a prescribed time on a specific month, date, hour, minute, or second or repeat every year, month, day, hour, minute, or second. It can also be programmed to go off while the M41ST85Y/W is in the battery back-up to serve as a system wake-up call. Bits RPT5–RPT1 put the alarm in the repeat mode of operation. Table 4, page 17 shows the possible configurations. Codes not listed in the table default to the once per second mode to quickly alert the user of an incorrect alarm setting.

When the clock information matches the alarm clock settings based on the match criteria defined by RPT5–RPT1, the AF (Alarm Flag) is set. If AFE (Alarm Flag Enable) is also set, the alarm condi-

tion activates the  $\overline{IRQ}/FT/OUT$  pin. To disable alarm, write '0' to the Alarm Date Register and to RPT5–RPT1. The  $\overline{IRQ}/FT/OUT$  output is cleared by a read to the Flags register. This read of the Flags register will also reset the Alarm Flag (D6; Register 0Fh).

The IRQ/FT/OUT pin can also be activated in the battery back-up mode. The IRQ/FT/OUT will go low if an alarm occurs and both ABE (Alarmin Battery Back-up Mode Enable) and AFE are set. The ABE and AFE bits are reset during power-up, therefore an alarm generated during power-up will only set AF. The user can read the Flag Register at system boot-up to determine if an alarm was generated while the M41ST85Y/W was in the deselect mode during power-up. Figure 14, page 16 illustrates the back-up mode alarm timing.





OEh OFh 10h

ACTIVE FLAG

IRQ/FT/OUT

HIGH-Z

Al03664

Figure 15. Alarm Interrupt Reset Waveforms

**Table 4. Alarm Repeat Modes** 

- and the state of								
RPT5	RPT4	RPT3	RPT2	RPT1	Alarm Setting			
1	1	1	1	1	Once per Second			
1	1	1	1	0	Once per Minute			
1	1	1	0	0	Once per Hour			
1	1	0	0	0	Once per Day			
1	0	0	0	0	Once per Month			
0	0	0	0	0	Once per Year			

## **Watchdog Timer**

The watchdog timer can be used to detect an outof-control microprocessor. The user programs the watchdog timer by setting the desired amount of time-out into the Watchdog Register, address 09h. Bits BMB4-BMB0 store a binary multiplier and the two lower order bits RB1-RB0 select the resolution, where 00=1/16 second, 01=1/4 second, 10=1 second, and 11=4 seconds. The amount of timeout is then determined to be the multiplication of the five bit multiplier value with the resolution. (For example: writing 00001110 in the Watchdog Register = 3\*1 or 3 seconds). If the processor does not reset the timer within the specified period, the M41ST85Y/W sets the WDF (Watchdog Flag) and generates a watchdog interrupt or a microprocessor reset.

**Note:** If the Square Wave function is enabled, the accuracy of the Watchdog Timer will be a function of the selected resolution.

The most significant bit of the Watchdog Register is the Watchdog Steering Bit (WDS). When set to a '0', the watchdog will activate the  $\overline{IRQ/FT/OUT}$  pin when timed-out. When WDS is set to a '1', the watchdog will output a negative pulse on the  $\overline{RST}$  pin for t<sub>REC</sub>. The Watchdog register, FT, AFE, ABE and SQWE Bits will reset to a '0' at the end of a Watchdog time-out when the WDS bit is set to a '1'.

The watchdog timer can be reset by two methods: 1) a transition (high-to-low or low-to-high) can be applied to the Watchdog Input pin (WDI) or 2) the microprocessor can perform a write of the Watchdog Register. The time-out period then starts over. **Note:** The WDI pin should be tied to  $V_{SS}$  if not used.

In order to perform a software reset of the watchdog timer, the original time-out period can be written into the Watchdog Register, effectively restarting the count-down cycle.

Should the watchdog timer time-out, and the WDS bit is programmed to output an interrupt, a value of 00h needs to be written to the Watchdog Register in order to clear the IRQ/FT/OUT pin. This will also disable the watchdog function until it is again programmed correctly. A read of the Flags Register will reset the Watchdog Flag (Bit D7; Register 0Fh).

The watchdog function is automatically disabled upon power-up and the Watchdog Register is cleared. If the watchdog function is set to output to the IRQ/FT/OUT pin and the frequency test function is activated, the watchdog function prevails and the frequency test function is denied. The OUT function has the lowest priority and will only be enabled when the Watchdog Register (09h), AFE Bit and FT Bit are '0.'

## **Square Wave Output**

The M41ST85Y/W offers the user a programmable square wave function which is output on the SQW pin. RS3-RS0 bits located in 13h establish the square wave output frequency. These fre-

quencies are listed in Table 5. Once the selection of the SQW frequency has been completed, the SQW pin can be turned on and off under software control with the Square Wave Enable Bit (SQWE) located in Register 0Ah.

**Table 5. Square Wave Output Frequency** 

	Square V		Square	e Wave	
RS3	RS2	RS1	RS0	Frequency	Units
0	0	0	0	None	-
0	0	0	1	32.768	kHz
0	0	1	0	8.192	kHz
0	0	1	1	4.096	kHz
0	1	0	0	2.048	kHz
0	1	0	1	1.024	kHz
0	1	1	0	512	Hz
0	1	1	1	256	Hz
1	0	0	0	128	Hz
1	0	0	1	64	Hz
1	0	1	0	32	Hz
1	0	1	1	16	Hz
1	1	0	0	8	Hz
1	1	0	1	4	Hz
1	1	1	0	2	Hz
1	1	1	1	1	Hz

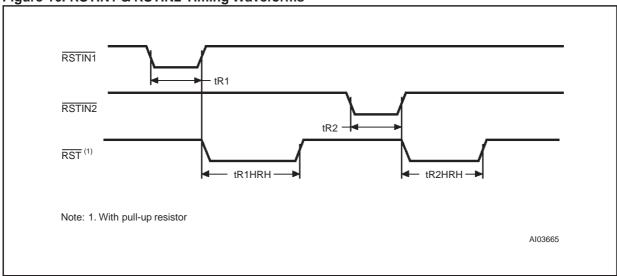
#### **Power-on Reset**

The M41ST85Y/W continuously monitors  $V_{CC}$ . When  $V_{CC}$  falls to the power fail detect trip point, the RST pulls low (open drain) and remains low on power-up for  $t_{REC}$  after  $V_{CC}$  passes  $V_{PFD}$ . The RST pin is an open drain output and an appropriate pull-up resistor should be chosen to control rise time.

## Reset Inputs (RSTIN1 & RSTIN2)

The M41ST85Y/W provides two independent inputs which can generate an output reset. The duration and function of these resets is identical to a reset generated by a power cycle. Table 6 and Figure 16 illustrate the AC reset characteristics of this function. Pulses shorter than  $t_{R1}$  and  $t_{R2}$  will not generate a reset condition.  $\overline{\text{RSTIN1}}$  and  $\overline{\text{RSTIN2}}$  are each internally pulled up to  $V_{CC}$  through a  $100 k\Omega$  resistor.





**Table 6. Reset AC Characteristics** 

Symbol	Parameter	Min	Max	Unit
t <sub>R1</sub> <sup>(1)</sup>	RSTIN1 Low to RSTIN1 High	200		ns
t <sub>R2</sub> <sup>(2)</sup>	RSTIN2 Low to RSTIN2 High	100		ms
t <sub>R1HRH</sub> (3)	RSTIN1 High to RST High	40	200	ms
t <sub>R2HRH</sub> (3)	RSTIN2 High to RST High	40	200	ms

Note: 1. Pulse width less than 50ns will result in no RESET (for noise immunity).

3.  $C_L = 5pF$  (see Figure 19, page 23).

<sup>2.</sup> Pulse width less than 20ms will result in no RESET (for noise immunity).

#### **Power-fail INPUT/OUTPUT**

The Power-Fail Input (PFI) is compared to an internal reference voltage (independent from the  $V_{PFD}$  comparator). If PFI is less than the power-fail threshold ( $V_{PFI}$ ), the Power-Fail Output ( $\overline{PFO}$ ) will go low. This function is intended for use as an undervoltage detector to signal a failing power supply. Typically PFI is connected through an external voltage divider (see Figure 4, page 6) to either the unregulated DC input (if it is available) or the regulated output of the  $V_{CC}$  regulator. The voltage divider can be set up such that the voltage at PFI falls below  $V_{PFI}$  several milliseconds before the regulated  $V_{CC}$  input to the M41ST85Y/W or the microprocessor drops below the minimum operating voltage.

During battery back-up, the power-fail comparator turns off and PFO goes (or remains) low. This occurs after V<sub>CC</sub> drops below V<sub>PFD</sub>(min). When power returns, PFO is forced high, irrespective of V<sub>PFI</sub> for the write protect time (t<sub>REC</sub>), which is the time from V<sub>PFD</sub>(max) until the inputs are recognized. At the end of this time, the power-fail comparator is enabled and PFO follows PFI. If the comparator is unused, PFI should be connected to V<sub>SS</sub> and PFO left unconnected.

## Calibrating the Clock

The M41ST85Y/W is driven by a quartz controlled oscillator with a nominal frequency of 32,768 Hz. The devices are tested not exceed +/–35 PPM (parts per million) oscillator frequency error at 25°C, which equates to about +/–1.53 minutes per month. When the Calibration circuit is properly employed, accuracy improves to better than +1/–2 PPM at 25°C.

The oscillation rate of crystals changes with temperature (see Figure 17, page 21). Therefore, the M41ST85Y/W design employs periodic counter correction. The calibration circuit adds or subtracts counts from the oscillator divider circuit at the divide by 256 stage, as shown in Figure 18, page 21. The number of times pulses which are blanked (subtracted, negative calibration) or split (added, positive calibration) depends upon the value loaded into the five Calibration bits found in the Control Register. Adding counts speeds the clock up, subtracting counts slows the clock down.

The Calibration bits occupy the five lower order bits (D4-D0) in the Control Register (8h). These bits can be set to represent any value between 0 and 31 in binary form. Bit D5 is a Sign bit; '1' indicates positive calibration, '0' indicates negative calibration. Calibration occurs within a 64 minute cycle. The first 62 minutes in the cycle may, once per minute, have one second either shortened by

128 or lengthened by 256 oscillator cycles. If a binary '1' is loaded into the register, only the first 2 minutes in the 64 minute cycle will be modified; if a binary 6 is loaded, the first 12 will be affected, and so on.

Therefore, each calibration step has the effect of adding 512 or subtracting 256 oscillator cycles for every 125,829,120 actual oscillator cycles, that is +4.068 or -2.034 PPM of adjustment per calibration step in the calibration register. Assuming that the oscillator is running at exactly 32,768 Hz, each of the 31 increments in the Calibration byte would represent +10.7 or -5.35 seconds per month which corresponds to a total range of +5.5 or -2.75 minutes per month.

Two methods are available for ascertaining how much calibration a given M41ST85Y/W may require.

The first involves setting the clock, letting it run for a month and comparing it to a known accurate reference and recording deviation over a fixed period of time. Calibration values, including the number of seconds lost or gained in a given period, can be found in Application Note AN934: TIMEKEEPER CALIBRATION. This allows the designer to give the end user the ability to calibrate the clock as the environment requires, even if the final product is packaged in a non-user serviceable enclosure. The designer could provide a simple utility that accesses the Calibration byte.

The second approach is better suited to a manufacturing environment, and involves the use of the IRQ/FT/OUT pin. The pin will toggle at 512Hz, when the Stop bit (ST, D7 of 1h) is '0', the Frequency Test bit (FT, D6 of 8h) is '1', the Alarm Flag Enable bit (AFE, D7 of Ah) is '0', and the Watchdog Steering bit (WDS, D7 of 9h) is '1' or the Watchdog Register (9h=0) is reset.

Any deviation from 512 Hz indicates the degree and direction of oscillator frequency shift at the test temperature. For example, a reading of 512.010124 Hz would indicate a +20 PPM oscillator frequency error, requiring a –10 (XX001010) to be loaded into the Calibration Byte for correction. Note that setting or changing the Calibration Byte does not affect the Frequency test output frequency.

The  $\overline{IRQ}/FT/OUT$  pin is an open drain output which requires a pull-up resistor to  $V_{CC}$  for proper operation. A 500 to10k resistor is recommended in order to control the rise time. The FT bit is cleared on power-down.

## **Output Driver Pin**

When the FT bit, AFE bit and watchdog register are not set, the IRQ/FT/OUT pin becomes an output driver that reflects the contents of D7 of the Control Register. In other words, when D6 of location 08h is a '0', D7 of location 08h and 0Ah and the watchdog register are a '0' then the IRQ/FT/OUT pin will be driven low.

**Note:** The IRQ/FT/OUT pin is an open drain which requires an external pull-up resistor.

#### **Initial Power-on Defaults**

Upon initial application of power to the device, the following register bits are set to a '0' state: Watchdog Register; FT; AFE; ABE and SQWE. The following bits are set to a '1' state: ST; OUT; and HT.

## **Century Bit**

Bits D7 and D6 of Clock Register 03h contain the CENTURY ENABLE Bit (CEB) and the CENTURY Bit (CB). Setting CEB to a "1" will cause CB to toggle, either from a "0" to "1" or from "1" to "0" at the turn of the century (depending upon its initial state). If CEB is set to a "0", CB will not toggle.

Figure 17. Crystal Accuracy Across Temperature

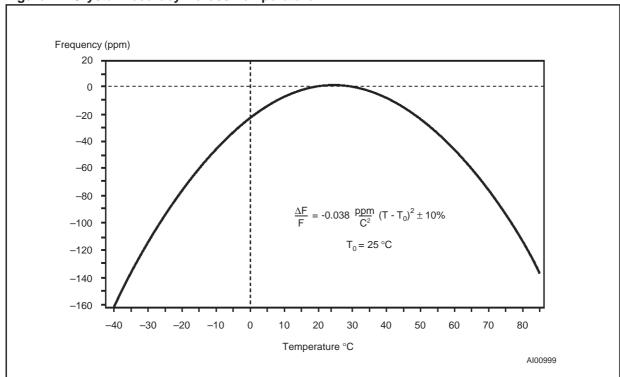
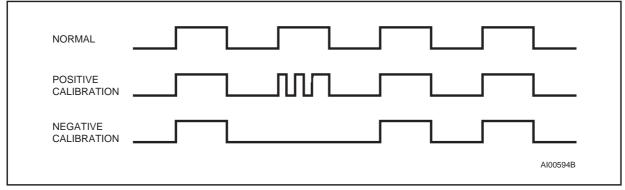


Figure 18. Calibration Waveform



## **MAXIMUM RATING**

Stressing the device above the rating listed in the Absolute Maximum Ratings" table may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those indicated in the Operating sections of this specification is not im-

plied. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability. Refer also to the STMicroelectronics SURE Program and other relevant quality documents.

**Table 7. Absolute Maximum Ratings** 

Symbol	Parameter		Value	Unit
T <sub>STG</sub>	Storage Temperature (VCC Off, Oscillator	SNAPHAT	-40 to 85	°C
1516	Off)	SOIC	-55 to 125	°C
T <sub>SLD</sub> (1)	Lead Solder Temperature for 10 seconds		260	°C
V <sub>IO</sub>	Input or Output Voltage		-0.3 to V <sub>CC</sub> +0.3	V
Vcc	Supply Voltage	M41ST85Y	-0.3 to 7	V
VCC	Supply Voltage	M41ST85W	-0.3 to 4.6	V
Io	Output Current		20	mA
PD	Power Dissipation		1	W

Note: 1. Soldering temperature not to exceed 260°C for 10 seconds (total thermal budget not to exceed 150°C for longer than 30 seconds). CAUTION: Negative undershoots below –0.3V are not allowed on any pin while in the Battery Back-up mode.

CAUTION: Do NOT wave solder SOIC to avoid damaging SNAPHAT sockets.

## DC AND AC PARAMETERS

This section summarizes the operating and measurement conditions, as well as the DC and AC characteristics of the device. The parameters in the following DC and AC Characteristic tables are derived from tests performed under the Measure-

ment Conditions listed in the relevant tables. Designers should check that the operating conditions in their projects match the measurement conditions when using the quoted parameters.

**Table 8. DC and AC Measurement Conditions** 

Parameter	M41ST85Y	M41ST85W
V <sub>CC</sub> Supply Voltage	4.5 to 5.5V	2.7 to 3.6V
Ambient Operating Temperature	−40 to 85°C	−40 to 85°C
Load Capacitance (C <sub>L</sub> )	100pF	50pF
Input Rise and Fall Times	≤ 50ns	≤ 50ns
Input Pulse Voltages	0.2 to 0.8V <sub>CC</sub>	0.2 to 0.8V <sub>CC</sub>
Input and Output Timing Ref. Voltages	0.3 to 0.7V <sub>CC</sub>	0.3 to 0.7V <sub>CC</sub>

Note: Output High Z is defined as the point where data is no longer driven (see Table 11, page 25).

Figure 19. AC Testing Load Circuit

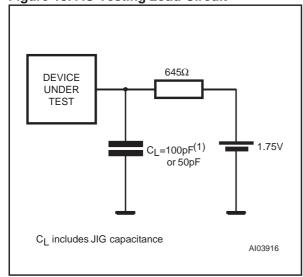
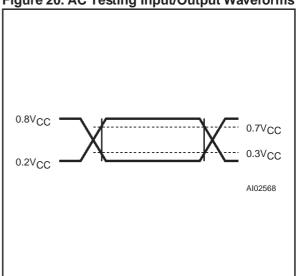


Figure 20. AC Testing Input/Output Waveforms



Note: 1.  $C_L = 100pF$  for the M41ST85Y, 50pF for the M41ST85W

Table 9. Capacitance

Symbol	Parameter	Min	Max	Unit
C <sub>IN</sub>	Input Capacitance		7	pF
C <sub>OUT</sub> (1)	Output Capacitance		10	pF
t <sub>LP</sub>	Low-pass filter input time constant (SDA and SCL)		50	ns

Note: Effective capacitance measured with power supply at 5V. Outputs are deselected.

1. Sampled only, not 100% tested.

**Table 10. DC Characteristics** 

Symb.	Parameter		Test Condition	Min	Тур	Max	Unit
I <sub>BAT</sub> (6)	Battery Current OSC ON		$T_A = 25^{\circ}C, V_{CC} = 0V,$		400	500	nA
IBAT\*'	Battery Current OSC OFF		V <sub>BAT</sub> = 3V		50		nA
ICC1	Supply Current	M41ST85Y	f = 400kHz			1.4	mA
1001	Supply Current	M41ST85W	1 = 400KHZ			750	μΑ
I <sub>CC2</sub>	Supply Current (Standby)	M41ST85Y	SCL, SDA = V <sub>CC</sub> - 0.3V			1	mA
1002	Supply Current (Standby)	M41ST85W	30L, 3DA = VCC = 0.3V			500	μΑ
ILI <sup>(1,2)</sup>	Input Leakage Current		$0 \text{A} \leq \text{A}^{\text{IN}} \leq \text{A}^{\text{CC}}$			±1	μΑ
ILI('',=/	Input Leakage Current (PF	l)	$0V \le V_{IN} \le V_{CC}$	-25	2	25	nA
I <sub>LO</sub> <sup>(1)</sup>	Output Leakage Current		0V ≤ V <sub>OUT</sub> ≤ V <sub>CC</sub>			±1	μΑ
. (5)	V <sub>OUT</sub> Current (Active)	M41ST85Y	V <sub>OUT1</sub> > V <sub>CC</sub> - 0.3V			175	mA
I <sub>OUT1</sub> <sup>(5)</sup>	VOUT Current (Active)	M41ST85W				100	mA
I <sub>OUT2</sub>	V <sub>OUT</sub> Current (Battery Back	r-up)	$V_{OUT2} > V_{BAT} - 0.3V$			100	μΑ
V <sub>IH</sub>	Input High Voltage			0.7V <sub>C</sub> C		VCC + 0.3	V
V <sub>IL</sub>	Input Low Voltage			-0.3		0.3V <sub>CC</sub>	V
V <sub>BAT</sub>	Battery Voltage				3.0		V
V <sub>OH</sub>	Output High Voltage		$I_{OH} = -1.0$ mA	2.4			V
V <sub>OHB</sub> <sup>(4)</sup>	V <sub>OH</sub> (Battery Back-up)		I <sub>OUT2</sub> = -1.0μA	2.5	2.9	3.6	V
V	Output Low Voltage		I <sub>OL</sub> = 3.0mA			0.4	V
V <sub>OL</sub>	Output Low Voltage (Open Drain) (3)		I <sub>OL</sub> = 10mA			0.4	V
V <sub>PFD</sub>	Power Fail Deselect	M41ST85Y		4.30	4.40	4.50	V
V PFD	M41ST85W			2.60	2.65	2.70	V
$V_{PFI}$	PFI Input Threshold			1.225	1.250	1.275	٧
V <sub>SO</sub>	Battery Back-up Switchove	r			2.5		V

Note: 1. Outputs Deselected.
2. RSTIN1 and RSTIN2 internally pulled-up to V<sub>CC</sub> through 100KΩ resistor. WDI internally pulled-down to V<sub>SS</sub> through 100KΩ resistor.
3. For IRQ/FT/OUT, RST pins (Open Drain).
4. Conditioned output (Ē<sub>CON</sub>) can only sustain CMOS leakage current in the battery back-up mode. Higher leakage currents will re-

<sup>5.</sup> External SRAM must match RTC SUPERVISOR chip V<sub>CC</sub> specification.

<sup>6.</sup> Measured with  $V_{OUT}$  and  $\overline{E}_{CON}\, open.$ 

**Table 11. Operating Modes** 

Mode	V <sub>CC</sub>	Ē	G	W	DQ0-DQ7	Power
Deselect		V <sub>IH</sub>	Х	Х	High Z	Standby
Write	4.5 to 5.5V or	V <sub>IL</sub>	Х	V <sub>IL</sub>	D <sub>IN</sub>	Active
Read	3.0 to 3.6V	V <sub>IL</sub>	V <sub>IL</sub>	V <sub>IH</sub>	D <sub>OUT</sub>	Active
Read		V <sub>IL</sub>	V <sub>IH</sub>	V <sub>IH</sub>	High Z	Active
Deselect	V <sub>SO</sub> to V <sub>PFD</sub> (min) <sup>(1)</sup>	Х	Х	Х	High Z	CMOS Standby
Deselect	≤ V <sub>SO</sub> <sup>(1)</sup>	Х	Х	Х	High Z	Battery Back-up Mode

Note: X = V<sub>IH</sub> or V<sub>IL</sub>.

**Table 12. Crystal Electrical Characteristics** 

Symbol	Parameter	Тур	Min	Max	Unit
f <sub>0</sub>	Resonant Frequency	32.768			kHz
R <sub>S</sub>	Series Resistance			60	kΩ
C <sub>L</sub> <sup>(1)</sup>	Load Capacitance	12.5			pF

Note: These are externally supplied

 $\textit{KDS} \ can \ be \ contacted \ at \ kouhou@kdsj.co.jp \ or \ http://www.kdsj.co.jp \ for \ further \ information \ on \ this \ crystal \ type.$ 

<sup>7.</sup> See Table 10, page 24 for details.

Load capacitors are integrated within the M41ST85Y/W. Circuit board layout considerations for the 32.768 kHz crystal of minimum trace lengths and isolation from RF generating signals should be taken into account.

ST Microelectronics recommends the KDS DT-38 Tuning Fork Type (thru-hole) or DMX-26 (SMD) quartz crystal for industrial temperature operations.

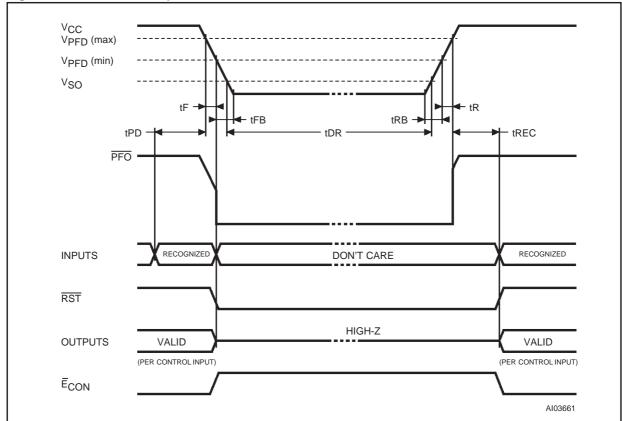


Figure 21. Power Down/Up Mode AC Waveforms

Table 13. Power Down/Up AC Characteristics

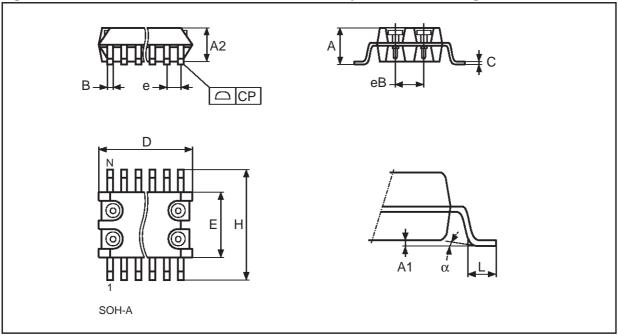
Symbol	Parameter	Min	Тур	Max	Unit
t <sub>F</sub> <sup>(1)</sup>	V <sub>PFD</sub> (max) to V <sub>PFD</sub> (min) V <sub>CC</sub> Fall Time	300			μs
t <sub>FB</sub> <sup>(2)</sup>	V <sub>PFD</sub> (min) to V <sub>SS</sub> V <sub>CC</sub> Fall Time	10			μs
t <sub>PD</sub>	EX at V <sub>IH</sub> before Power Down	0			μs
t <sub>PFD</sub>	PFI to PFO Propagation Delay		15	25	μs
t <sub>R</sub>	V <sub>PFD</sub> (min) to V <sub>PFD</sub> (max) V <sub>CC</sub> Rise Time	10			μs
t <sub>RB</sub>	V <sub>SS</sub> to V <sub>PFD</sub> (min) V <sub>CC</sub> Rise Time	1			μs
trec	Power up Deselect Time	40		200	ms

Note: 1. V<sub>PFD</sub> (max) to V<sub>PFD</sub> (min) fall time of less than t<sub>F</sub> may result in deselection/write protection not occurring until 200µs after V<sub>CC</sub> passes V<sub>PFD</sub> (min).

<sup>2.</sup> V<sub>PFD</sub> (min) to V<sub>SS</sub> fall time of less than t<sub>FB</sub> may cause corruption of RAM data.

## **PACKAGE MECHANICAL**

Figure 22. SOH28 - 28 lead Plastic Small Outline, Battery SNAPHAT, Package Outline



Note: Drawing is not to scale.

Table 14. SOH28 - 28 lead Plastic Small Outline, battery SNAPHAT, Package Mechanical Data

Symbol		millimeters			inches	
Symbol	Тур	Min	Max	Тур	Min	Max
А			3.05			0.120
A1		0.05	0.36		0.002	0.014
A2		2.34	2.69		0.092	0.106
В		0.36	0.51		0.014	0.020
С		0.15	0.32		0.006	0.012
D		17.71	18.49		0.697	0.728
E		8.23	8.89		0.324	0.350
е	1.27	_	-	0.050	-	-
eB		3.20	3.61		0.126	0.142
Н		11.51	12.70		0.453	0.500
L		0.41	1.27		0.016	0.050
α		0°	8°		0°	8°
N	28			28	-	
СР			0.10			0.004

Figure 23. SH - SNAPHAT Housing for 48 mAh Battery & Crystal, Package Outline

Note: Drawing is not to scale.

Table 15. SH - SNAPHAT Housing for 48 mAh Battery & Crystal, Package Mechanical Data

Symbol		millimeters			inches	
	Тур	Min	Max	Тур	Min	Max
А			9.78			0.3850
A1		6.73	7.24		0.2650	0.2850
A2		6.48	6.99		0.2551	0.2752
А3			0.38			0.0150
В		0.46	0.56		0.0181	0.0220
D		21.21	21.84		0.8350	0.8598
E		14.22	14.99		0.5598	0.5902
eA		15.55	15.95		0.6122	0.6280
eB		3.20	3.61		0.1260	0.1421
L		2.03	2.29		0.0799	0.0902

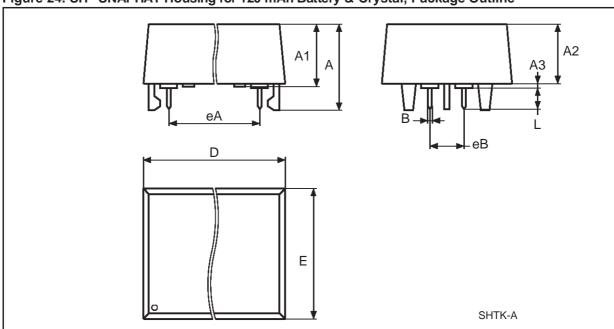


Figure 24. SH - SNAPHAT Housing for 120 mAh Battery & Crystal, Package Outline

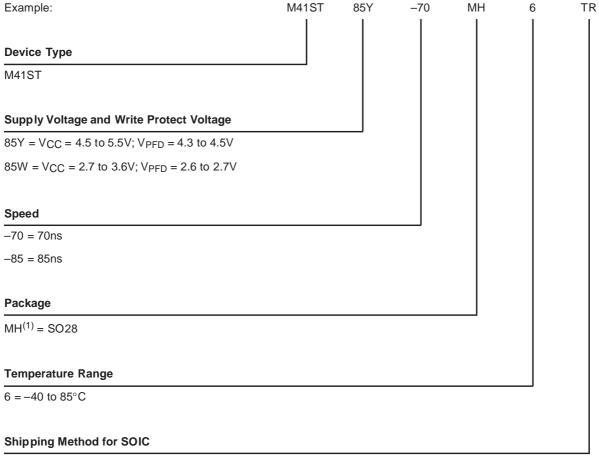
Note: Drawing is not to scale.

Table 16. SH - SNAPHAT Housing for 120 mAh Battery & Crystal, Package Mechanical Data

Symbol		millimeters			inches	
Symbol	Тур	Min	Max	Тур	Min	Max
А			10.54			0.4150
A1		6.73	7.24		0.2650	0.2850
A2		6.48	6.99		0.2551	0.2752
А3			0.38			0.0150
В		0.46	0.56		0.0181	0.0220
D		21.21	21.84		0.8350	0.8598
E		14.22	14.99		0.5598	0.5902
eA		15.55	15.95		0.6122	0.6280
eB		3.20	3.61		0.1260	0.1421
L		2.03	2.29		0.0799	0.0902

## **PART NUMBERING**

## **Table 17. Ordering Information Scheme**



blank = Tubes

TR = Tape & Reel

Note: 1. The 28-pin SOIC package (SOH28) requires the battery/crystal package (SNAPHAT) which is ordered separately under the part number "M4TXX-BR12SHX" in plastic tube or "M4TXX-BR12SHXTR" in Tape & Reel form.

Caution: Do not place the SNAPHAT battery package "M4TXX-BR12SH" in conductive foam since will drain the lithium button-cell battery.

For a list of available options (e.g., Speed, Package) or for further information on any aspect of this device, please contact the ST Sales Office nearest to you.

**Table 18. SNAPHAT Battery Table** 

Part Number Description		Package
M4T28-BR12SH	Lithium Battery (48mAh) and Crystal SNAPHAT	SH
M4T32-BR12SH	Lithium Battery (120mAh) and Crystal SNAPHAT	SH

## **REVISION HISTORY**

## **Table 19. Document Revision History**

Date	Revision Details
August 2000	First issue
08/24/00	Block Diagram added (Figure 3)
10/12/00	t <sub>REC</sub> Table removed, cross references corrected
12/18/00	Reformatted, TOC added, and PFI Input Leakage Current added (Table 10)

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